## **Electronic Supplementary Information (ESI)**

# Mesoporous Alloy Chiral Nanoparticles with High Production Yield and Strong Optical Activities

Yicong Ma,<sup>a</sup> Lin Yang,<sup>b</sup> Yu Chen,<sup>c</sup> Xiaopeng Bai,<sup>d</sup> Geping Qu,<sup>e</sup> Tao Yao,<sup>f</sup> Xiangchen Hu,<sup>c</sup> Jianfang Wang,<sup>d</sup> Zongxiang Xu,<sup>e</sup> Yi Yu,<sup>c</sup> and Zhifeng Huang<sup>\*f</sup>

<sup>a</sup>Department of Physics, Hong Kong Baptist University (HKBU), Kowloon Tong, Hong Kong SAR, China

<sup>b</sup>HKBU Institute for Research and Continuing Education Shenzhen, Guangdong 518057, China

<sup>c</sup>School of Physical Science and Technology, ShanghaiTech University, Shanghai, 201210, China

<sup>d</sup>Department of Physics, The Chinese University of Hong Kong, Shatin, NT, Hong Kong SAR, China

<sup>e</sup>Department of Chemistry, Southern University of Science and Technology, Shenzhen, Guangdong, 518055, China

<sup>f</sup>Department of Chemistry, The Chinese University of Hong Kong, Shatin, NT, Hong Kong SAR, China

E-mail: zfhuang@cuhk.edu.hk

#### **Experimental Methods**

#### GLAD of the host Ag CNPs

The host CNPs were made of Ag. In a custom-built physical vapor deposition system (JunSun Tech Co. Ltd., Taiwan) with a high vacuum of  $10^{-7}$ - $10^{-6}$  Torr, metal pellets (Ag (99.999%)), Fuzhou Innovation Photoelectric Technology Co., China) were evaporated at a rate of  $\approx 0.3$  nm s<sup>-1</sup> as monitored by a quartz crystal microbalance (QCM) located near a substrate, using an electron-beam accelerating voltage of 8.0 kV, and emission current of 17–20 mA. At a deposition angle (*a*) of 86° with respect to the normal direction of a substrate, Ag was evaporated on Si wafers (Semiconductor Wafer Inc., Taiwan) and sapphires (Meco Technology Ltd., Hong Kong) in an area of  $1.5 \times 1.5$  cm<sup>2</sup>. The substrate temperature was controlled at  $\approx$ -45 °C, using an ethanol cooling system. To produce the RH- and LH-host with a given nominal helical pitch *P*, a substrate was rotated in clockwise and counterclockwise, respectively, at a rate  $R_r$  (in units of degree per second, or ° s<sup>-1</sup>) given by  $R_r = 360 R_d/P_d$  (S1)

where  $R_d$  is the deposition rate of Ag at the substrate surface calibrated as 0.045 nm s<sup>-1</sup> at *a* of 86°, and  $P_d$  is the as-designed nominal *P*. The nominal *P* was experimentally evaluated by P = H/m (S2) where *H* is the CNP height measured with scanning electron microscopy (SEM, Oxford, LEO)

1530), and m is the number of substrate rotation during GLAD.

### Physical vapor deposition of Au adhesion layers

The Au adhesion layer was deposited with Au (99.999%, Fuzhou Innovation Photoelectric Technology Co., China) at *a* of 0° and  $R_d = 0.3$  nm s<sup>-1</sup>, with an electron-beam accelerating voltage of 8.0 kV and emission current of 68–70 mA. The substrate was not rotated ( $R_r = 0$  ° s<sup>-1</sup>), and the substrate temperature was controlled as ≈-45 °C.  $T_{AL}$  was adjusted as a function of deposition duration.

### GLAD of the host Ag<sub>1-x</sub>Au<sub>x</sub> CNPs

GLAD of the host binary  $Ag_{1-x}Au_x$  CNPs involved three sequential GLAD processes. The first and third step was the GLAD of the host Ag CNPs having a nominal *P* of roughly 8 nm and *H* of 40 nm. The second step was the deposition of dopant Au on the Ag CNPs, performed at *a* of 86°, substrate temperature of  $\approx$  -45 °C,  $R_r = 0$  ° s<sup>-1</sup> (without substrate rotation) and  $R_d = 0.3$ nm s<sup>-1</sup>, using an electron-beam accelerating voltage of 8.0 kV and emission current of 68–70 mA. The binary host was deposited on the adhesion layer of Au covering the supporting substrate.

#### GRR of the host

In a homemade Teflon beaker, sapphire and silicon substrates deposited with the host were insert in a homemade Teflon holder and then immersed into a 200-mL electrolyte containing 20  $\mu$ mol L<sup>-1</sup> chloroauric acid (HAuCl<sub>4</sub>·3H<sub>2</sub>O, 99.999%, Sigma-Aldrich) at a stirring rate of 380 rpm under 25°C. Before the GRR, the Teflon holder and beaker were degreased in Piranha (98% H<sub>2</sub>SO<sub>4</sub>: 30% H<sub>2</sub>O<sub>2</sub> = 3:1, v/v) for 15 min at room temperature, sufficiently rinsed with DI water (18.2 MΩ, Milli-Q reference water purification system fed with campus distilled water), and dried with N<sub>2</sub> gases. After the GRR for 1–2 hr, the samples were removed out of the electrolyte to terminate the GRR and thoroughly rinsed with DI water and dried with N<sub>2</sub> gases.

#### **Optical Characterization**

Under ambient conditions, BioLogic CD (MOS 500) was used to monitor UV–visible–NIR extinction and CD spectra of a close-packed CNP array deposited on sapphire, under an irradiative incidence along the normal direction of sapphires. An extinction spectrum was monitored with an irradiation of linearly polarized light. For a given sample, four CD spectra in a wavelength range of 200-800 nm were subsequently recorded. After monitoring a CD spectrum, the sample was manually rotated at an angle of 90° around its normal axis before measuring the next CD spectrum. Then, the four CD spectra were algebraically averaged to obtain a CD spectrum of the sample, to eliminate linear birefringence and linear dichroism.

#### **Structure Characterization**

The as-deposited samples were mechanically split, leaving the freshly exposed surfaces for the SEM-EDX (Carl Zeiss: LEO 1530) characterization. The CNPs were scratched off the substrates and well dispersed in water via ultrasonication for 30 min. Several drops of the mixture were applied to a TEM grid with lacey carbon film (Electron Microscopy Sciences, Inc., USA). The grid was dried under ambient conditions and characterized by TEM (Tecnai G2 20 STWIN). The High-resolution TEM, HAADF-STEM and EDS mapping were performed with a JEOL JEM-F200 field-emission gun microscope (200 kV, fitted with a JEOL silicon drift detector). Without post-deposition treatment, the samples were characterized by XRD (Bruker, non-monochromated Cu Ka X-ray with wavelength of 0.15418 nm, Advance

D8 multipurpose X-ray diffractometer) and XPS (ULVAC PHI 5000 VersaProbe III, Al Ka radiation of 1486.6 eV, at a current of 4.5 mA, voltage of 10 kV, and takeoff angle (between the sample and detector) of 45°, and in a vacuum of  $\approx 2 \times 10^{-9}$  mbar).



**Figure S1.** The GRR ( $t_{GRR}$  of 1 hr) of RH-Ag CNPs (with a nominal *P* of 8 nm and *H* of 80 nm) deposited on an Au adhesion layer with a  $T_{AL}$  of (a) 0 nm, (b)10 nm, (c) 20 nm, and (d) 30 nm. (I, II) Ag CNPs; (III, IV) Ag:Au m-CNPs. (I, III) SEM top-down images; (II, IV) SEM cross-sectional images. (b-II, c-II, and d-II) The red lines show  $T_{AL}$ .



**Figure S2.** The 1 hr-GRR of Ag CNPs (with a nominal *P* of 8 nm and height *H* of 80 nm) deposited on an Au adhesion layer with a  $T_{AL}$  of (I, II) 0 nm, (III, IV)10 nm, and (V, VI) 30 nm, characterized with the UV-visible-NIR spectroscopies of (a) extinction, (b) CD, and (c) anisotropic *g*-factor. (I, III, V) Ag CNPs; (II, IV, VI) Ag:Au m-CNPs produced with the 1-hr GRR. LH: red and pink lines; RH: blue and cyan lines.



**Figure S3.** The GRR of (a, b) RH-Ag<sub>0.75</sub>Au<sub>0.25</sub> and (c, d) RH-Ag<sub>0.80</sub>Au<sub>0.20</sub> CNPs deposited on the Au adhesion layer (with  $T_{AL}$  of 20 nm), with the  $t_{GRR}$  of (I) 0, (II) 1, (III) 1.5 and (IV) 2 hr. SEM (a, c) top-down and (b, d) tilted images. Scale bars: 100 nm.



**Figure S4.** The GRR of (a, b) RH-Ag<sub>0.85</sub>Au<sub>0.15</sub> and (c, d) RH-Ag<sub>0.90</sub>Au<sub>0.10</sub> CNPs deposited on the Au adhesion layer (with  $T_{AL}$  of 20 nm), with the  $t_{GRR}$  of (I) 0, (II) 1, (III) 1.5 and (IV) 2 hr. SEM (a, c) top-down and (b, d) tilted images. Scale bars: 100 nm.



**Figure S5.** The GRR of Ag CNPs deposited on the Au adhesion layer with  $T_{AL}$  of (I) 0 nm and (II) 20 nm with the  $t_{GRR}$  increasing from 0 to 2 hr, characterized with UV-visible-NIR spectroscopies of (a) extinction, (b) CD, and (c) anisotropic *g*-factor. LH: red lines; RH: blue lines.



**Figure S6.** The GRR of (I)  $Ag_{0.75}Au_{0.25}$ , (II)  $Ag_{0.80}Au_{0.20}$ , (III)  $Ag_{0.85}Au_{0.15}$ , and (III)  $Ag_{0.90}Au_{0.10}$  CNPs (deposited on the Au adhesion layer with the  $T_{AL}$  of 20 nm) with the  $t_{GRR}$  increasing from 0 to 2 hr, characterized with UV-visible-NIR spectroscopies of (a) extinction, (b) CD, and (c) anisotropic g-factor. LH: red lines; RH: blue lines.



**Figure S7.** Plots of PY versus *x* for the GRR of binary  $Ag_{(1-x)}Au_x$  CNPs (deposited on the Au adhesion layer with the  $T_{AL}$  of 20 nm) with the  $t_{GRR}$  of (I) 1 hr, (II) 1.5 hr, and (III) 2 hr. LH: red solid squares; RH: blue solid squares. The results for the GRR of LH- and RH-Ag CNPs (without the Au adhesion layer) are shown with red and blue hollow spheres, respectively.



**Figure S8.** Plot of atomic percentage (at.%) of Ag in the RH-Ag:Au m-CNPs versus  $t_{GRR}$ , for the GRR of RH-Ag<sub>(1-x)</sub>Au<sub>x</sub> CNPs deposited on the Au adhesion layer with the  $T_{AL}$  of 20 nm. x of 0.10 (Olive-green squares), 0.15 (blue squares), 0.20 (pink squares), and 0.25 (purple squares). The linear fitting leads to the evaluation of  $r_{GRR}$  as a function of x, as shown in **Figure 2c**.